

METHOD FOR MAKING A HETEROJUNCTION BIPOLAR TRANSISTOR

Abstract

The invention concerns a heterojunction bipolar transistor comprising a support, and epitaxially grown from said support, at least: one collecting, respectively emitting, layer; at least one base layer (B); and at least one emitting, respectively collecting, layer. The collecting, respectively emitting, layer comprises: at least one first undercoat (C1) contacted with said base layer, substantially of similar composition as said emitting, respectively collecting, layer; and at least one second undercoat (C2) on the side opposite said base layer relative to said first undercoat.

[Fig. 4a]